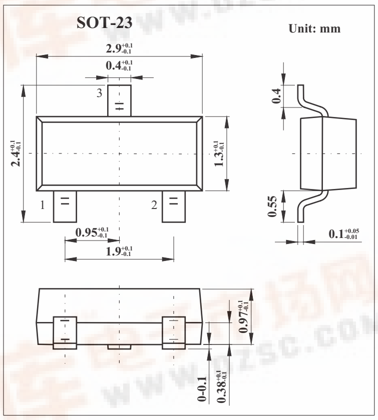
Silicon Schottky Diodes

BAT64 series



Features

- For low-loss,fast-recovery, meter protection bias isolation and clamping applications
- Integrated diffused guard ring
- Low forward current

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Max	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	250	mA
Average forward current (50/60Hz,sinus)	I_{FAV}	120	mA
Surge forward current (t ≤ 10 ms)	I_{FSM}	800	mA
Total power dissipation Ts = 61 ℃	P_{tot}	250	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃
Junction ambient (Note 1)	$R_{th\ JA}$	≤ 495	KW
Junction soldering point	$R_{th\ JS}$	≤ 355	KW

Note

1. Package mounted on epoxy pcb 40mm × 40 mmm × 1.5 mm /0.5cm^2 Cu

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	V_R = 25 V,T_A = 25 ℃			2	μA
		V_R = 25 V,T_A = 85 ℃			200	
Forward voltage	V_F	I_F = 1 mA		320	350	mV
		I_F = 10 mA		385	430	V
		I_F = 30 mA		440	520	V
		I_F = 100 mA		570	750	V
Diode capacitance	C_T	V_R = 1 V,f = 1 MHz		4	6	pF

Marking

Type	BAT64	BAT64-04	BAT64-05	BAT64-06
Marking	63s	64s	65s	66s